

isc Silicon NPN Power Transistors

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 200V(Min)
- · Fast Switching Speed
- · Low Saturation Voltage
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation



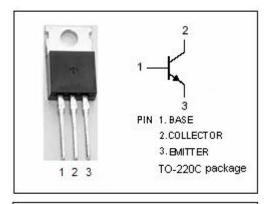
APPLICATIONS

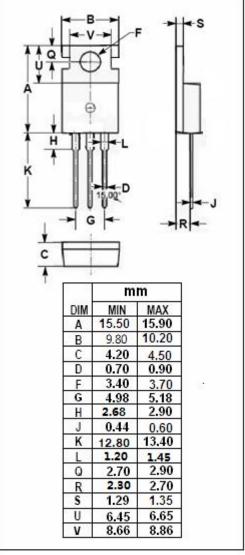
• Designed for high definition CRT display horizontal deflection output applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|---------------|--|
| V _{CBO} | Collector-Base Voltage | 400 | V | |
| Vceo | Collector-Emitter Voltage | 200 | V | |
| V _{EBO} | Emitter-Base Voltage 6 | | V | |
| lc | Collector Current-Continuous 7 | | Α | |
| Ісм | Collector Current-Peak | 12 | Α | |
| l _Β | Base Current-Continuous | 4 | Α | |
| P _T | Total Power Dissipation @ T _C =25℃ | 50 | W | |
| TJ | Junction Temperature | 150 | ${\mathbb C}$ | |
| T _{stg} | Storage Temperature Range | -55~150 | ${\mathbb C}$ | |







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2SC3591

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _E = 0 | 400 | | | V |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 1mA; R _{BE} = ∞ | 200 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1m A; I _C = 0 | 6 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 0.5A | | | 0.8 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | Ic= 5A; I _B = 0.5A | | | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 250V; I _E = 0 | | | 100 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 100 | μА |
| h _{FE-1} | DC Current Gain | Ic= 1A; VcE= 1V | 15 | | | |
| h _{FE-2} | DC Current Gain | I _C = 5A; V _{CE} = 1V | 10 | | 50 | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V | | 40 | | MHz |
| t _f | Fall Time | I _C = 5A, I _{B1} = -I _{B2} = 0.5A | | | 0.3 | μS |

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